materials

MDPI

Article

Weak Antilocalization Tailor-Made by System Topography in Large Scale Bismuth Antidot Arrays

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Supplementary Material

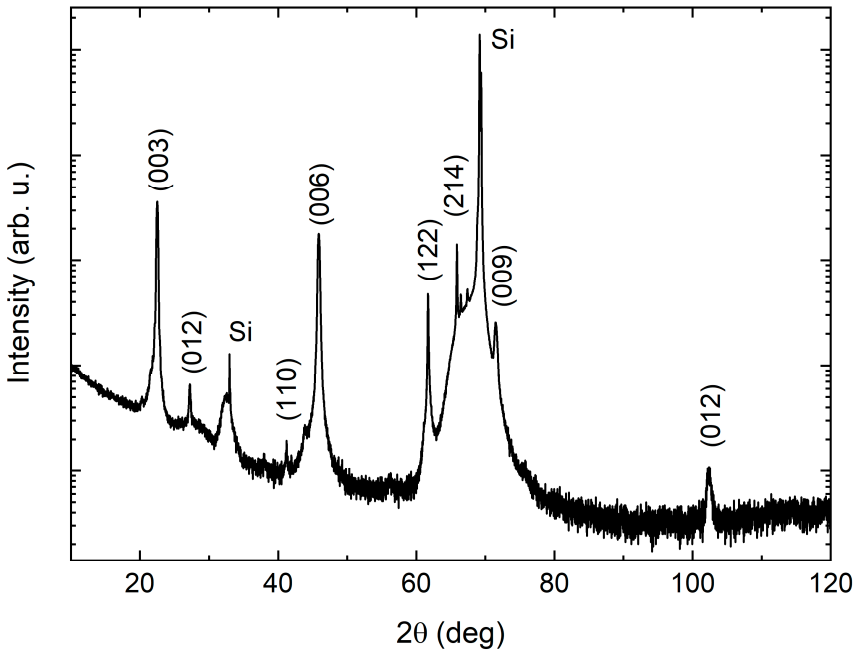

Figure S1. XRD pattern of the Bi (50 nm) thin film deposited on the flat Si/SiO_2 (100 nm) substrate.

Magnetotransport measurements for Bi arrays with antidot size of 45 nm and 110 nm.

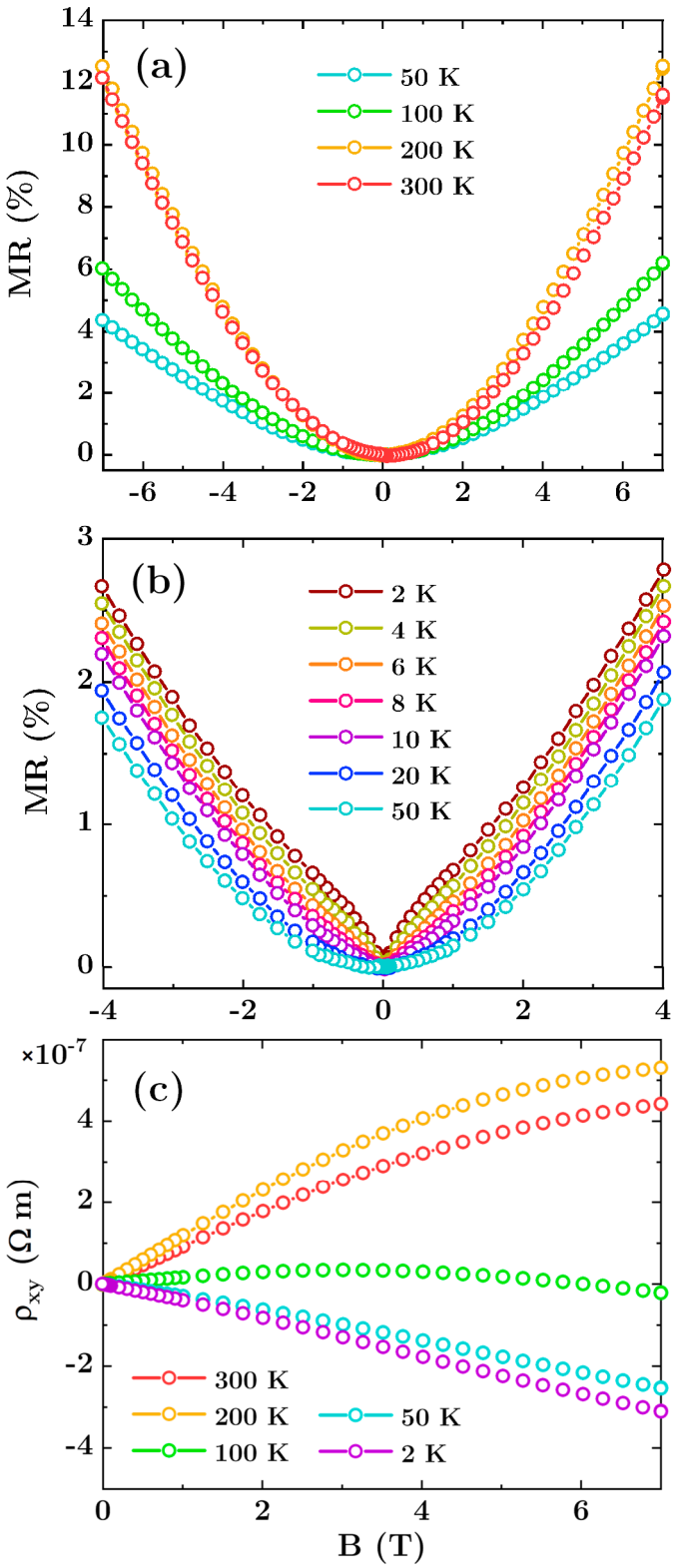

Figure S2. (**a**,**b**) Longitudinal magnetoresistance (MR) and (**c**) Hall transverse magnetoresistance vs field curves for Bi antidot arrays with antidot size of 45 nm. For clarity, the results of Hall measurements for temperature range 4 K – 20 K were omitted since they are similar to those obtained at 2 K and 50 K.

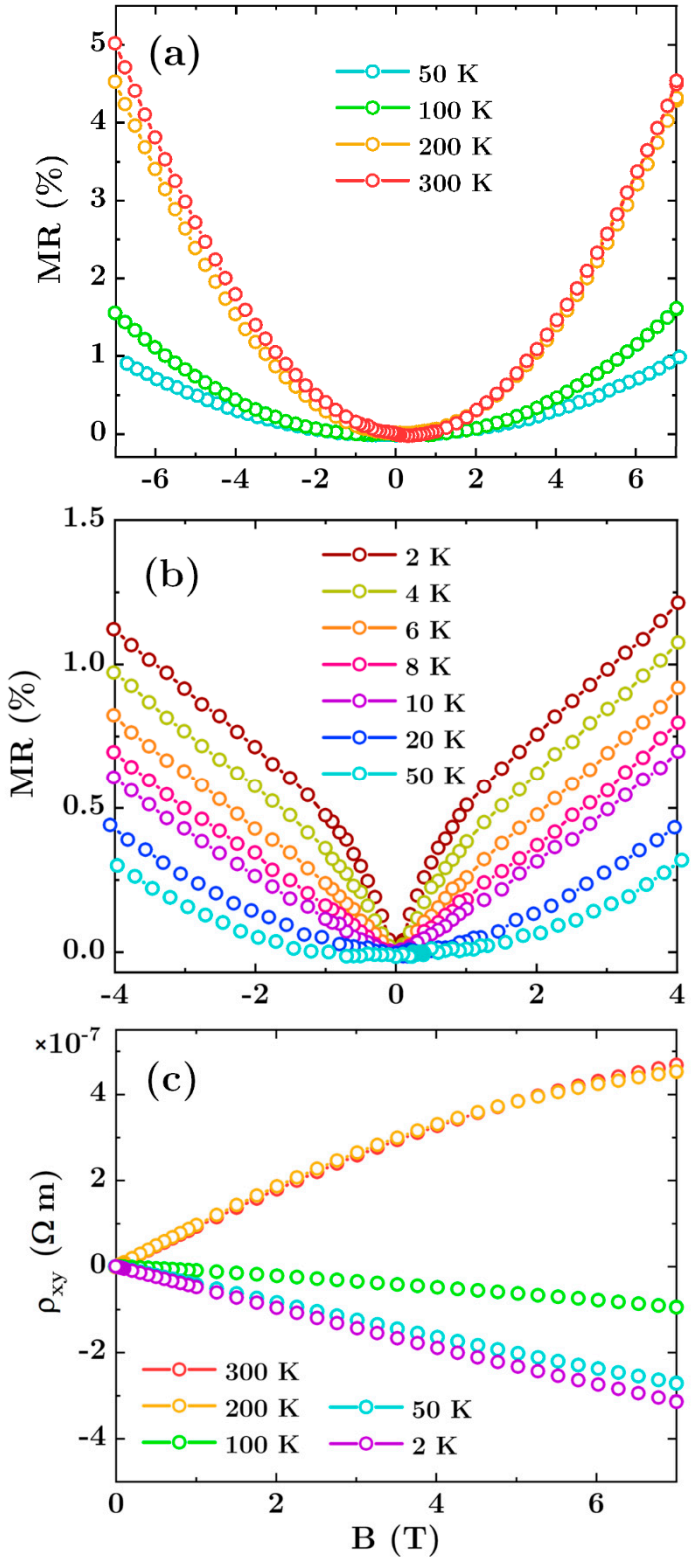

Figure S3. (**a**,**b**) Longitudinal magnetoresistance (MR) and (**c**) Hall transverse magnetoresistance vs field curves for Bi antidot arrays with antidot size of 110 nm. For clarity, the results of Hall measurements for temperature range 4 K–20 K were omitted since they are similar to those obtained at 2 K and 50 K.